

# MC74VHC00

## Quad 2-Input NAND Gate

The MC74VHC00 is an advanced high speed CMOS 2-input NAND gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

### Features

- High Speed:  $t_{PD} = 3.7 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \mu\text{A}$  (Max) at  $T_A = 25^\circ\text{C}$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.8 \text{ V}$  (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 32 FETs or 8 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

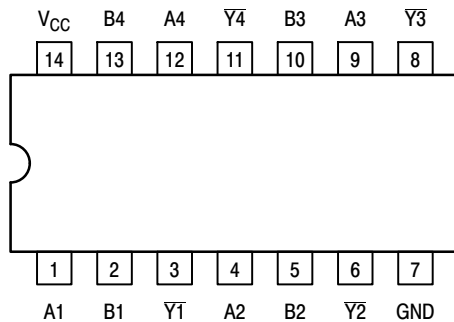


Figure 1. Pinout: 14-Lead Packages (Top View)

### FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L



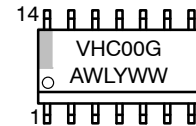
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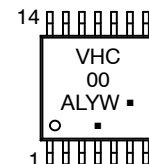
### MARKING DIAGRAMS



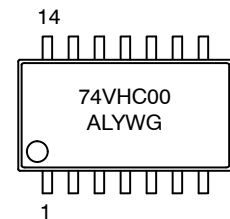
SO-14  
D SUFFIX  
CASE 751A



TSSOP-14  
DT SUFFIX  
CASE 948G



EIAJ SO-14  
M SUFFIX  
CASE 965



- A = Assembly Location
- L, WL = Wafer Lot
- Y = Year
- W, WW = Work Week
- G, ■ = Pb-Free Device

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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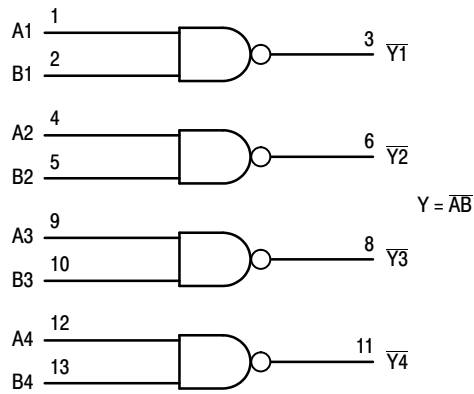


Figure 2. Logic Diagram

## MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CC}$	Positive DC Supply Voltage	-0.5 to +7.0	V
$V_{IN}$	Digital Input Voltage	-0.5 to +7.0	V
$V_{OUT}$	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	Input Diode Current	-20	mA
$I_{OK}$	Output Diode Current	$\pm 20$	mA
$I_{OUT}$	DC Output Current, per Pin	$\pm 25$	mA
$I_{CC}$	DC Supply Current, $V_{CC}$ and GND Pins	$\pm 75$	mA
$P_D$	Power Dissipation in Still Air	SOIC Package 200 TSSOP 180	mW
$T_{STG}$	Storage Temperature Range	-65 to +150	$^{\circ}C$
$V_{ESD}$	ESD Withstand Voltage	Human Body Model (Note 1) >2000 Machine Model (Note 2) >200 Charged Device Model (Note 3) N/A	V
$I_{LATCH-UP}$	Latch-Up Performance	Above $V_{CC}$ and Below GND at 125 $^{\circ}C$ (Note 4)	$\pm 300$
$\theta_{JA}$	Thermal Resistance, Junction to Ambient	SOIC Package 143 TSSOP 164	$^{\circ}C/W$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Tested to EIA/JESD22-A114-A
2. Tested to EIA/JESD22-A115-A
3. Tested to JESD22-C101-A
4. Tested to EIA/JESD78

## RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
$V_{CC}$	DC Supply Voltage	2.0	5.5	V
$V_{IN}$	DC Input Voltage	0	5.5	V
$V_{OUT}$	DC Output Voltage	0	$V_{CC}$	V
$T_A$	Operating Temperature Range, All Package Types	-55	125	$^{\circ}C$
$t_r, t_f$	Input Rise or Fall Time	$V_{CC} = 3.3 V \pm 0.3 V$ 0	100	ns/V
		$V_{CC} = 5.0 V \pm 0.5 V$ 0	20	

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## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	T <sub>A</sub> = 25°C			T <sub>A</sub> = -40 to 85°C		T <sub>A</sub> = -55 to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V <sub>IH</sub>	High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V <sub>CC</sub> × 0.7			1.50 V <sub>CC</sub> × 0.7		1.50 V <sub>CC</sub> × 0.7		V
V <sub>IL</sub>	Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V <sub>CC</sub> × 0.3		0.50 V <sub>CC</sub> × 0.3		0.50 V <sub>CC</sub> × 0.3	V
V <sub>OH</sub>	High-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = - 50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = - 4 mA I <sub>OH</sub> = - 8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.40 3.70		
V <sub>OL</sub>	Low-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 4 mA I <sub>OL</sub> = 8 mA	3.0 4.5			0.36 0.36	0.44 0.44		0.55 0.55		
I <sub>in</sub>	Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 2.0	μA
I <sub>CC</sub>	Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5			2.0		20		40	μA

## AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0 ns)

Symbol	Parameter	Test Conditions	T <sub>A</sub> = 25°C			T <sub>A</sub> = -40 to 85°C		T <sub>A</sub> = -55 to +125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, A or B to $\bar{Y}$	V <sub>CC</sub> = 3.3 ± 0.3 V    C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.5 8.0	7.9 11.4	1.0 1.0	9.5 13.0	1.0 1.0	10 14.5	ns
		V <sub>CC</sub> = 5.0 ± 0.5 V    C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		3.7 5.2	5.5 7.5	1.0 1.0	6.5 8.5	1.0 1.0	7.0 9.5	
C <sub>in</sub>	Input Capacitance			4.0 10			10		10	pF

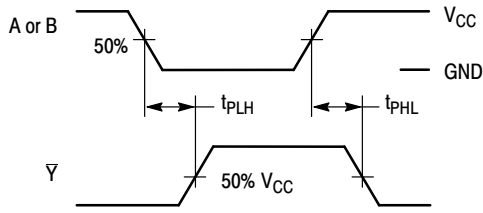
C <sub>PD</sub>	Power Dissipation Capacitance (Note 5)	Typical @ 25°C, V <sub>CC</sub> = 5.0 V		pF
		19		

5. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/4 (per gate). C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

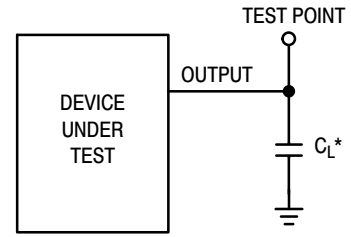
## NOISE CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0 ns, C<sub>L</sub> = 50 pF, V<sub>CC</sub> = 5.0 V, Measured in SOIC Package)

Symbol	Characteristic	T <sub>A</sub> = 25°C		Unit
		Typ	Max	
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	- 0.3	- 0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V

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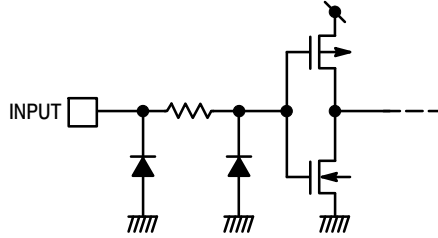


**Figure 3. Switching Waveforms**



\*Includes all probe and jig capacitance

**Figure 4. Test Circuit**



**Figure 5. Input Equivalent Circuit**

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC74VHC00DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHC00DTG	TSSOP-14* (Pb-Free)	96 Units / Rail
MC74VHC00DTR2G	TSSOP-14* (Pb-Free)	2500 / Tape & Reel
MC74VHC00MELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel

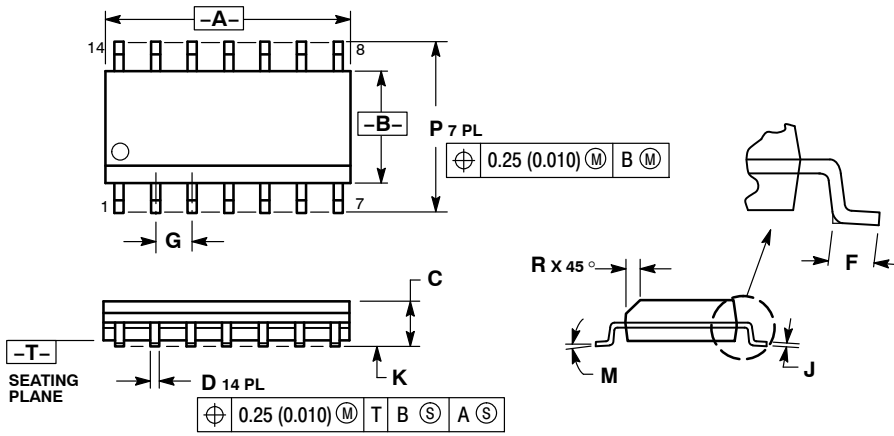
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*This package is inherently Pb-Free.

# MC74VHC00

## PACKAGE DIMENSIONS

SOIC-14  
CASE 751A-03  
ISSUE J

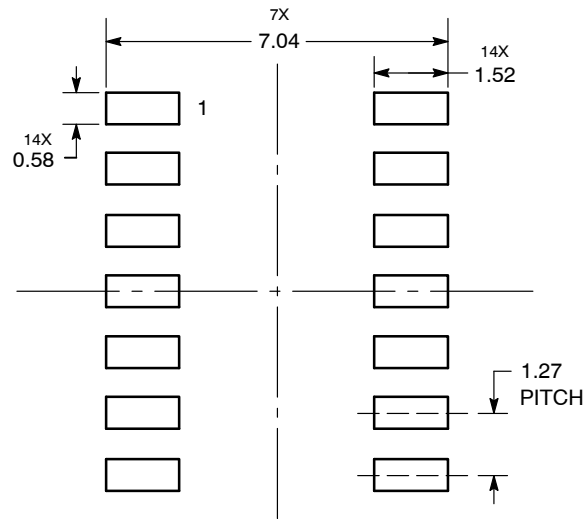


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0° - 7°		0° - 7°	
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

### SOLDERING FOOTPRINT

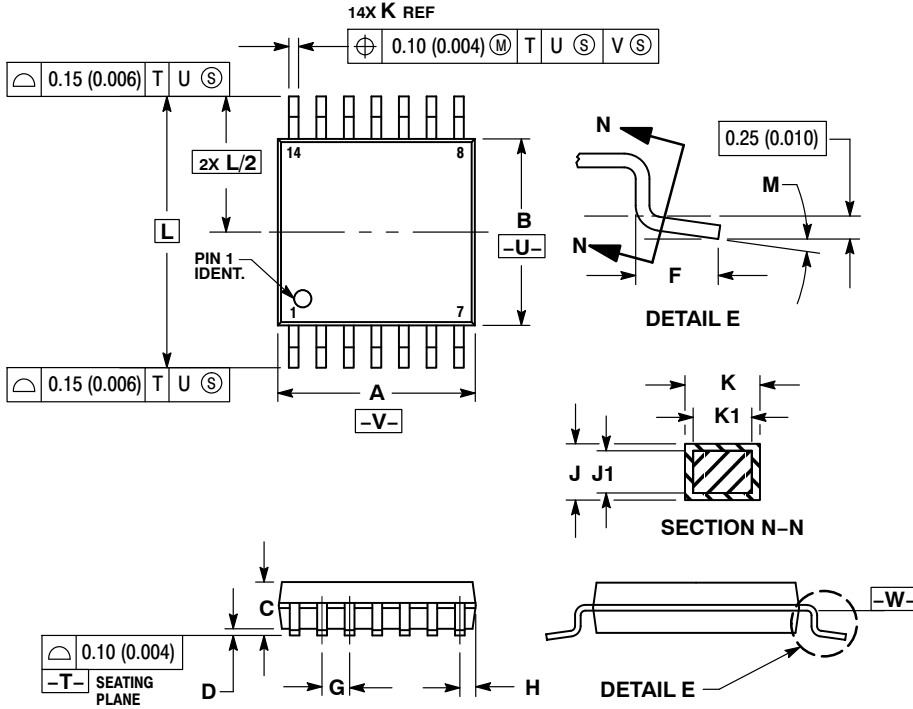


DIMENSIONS: MILLIMETERS

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## PACKAGE DIMENSIONS

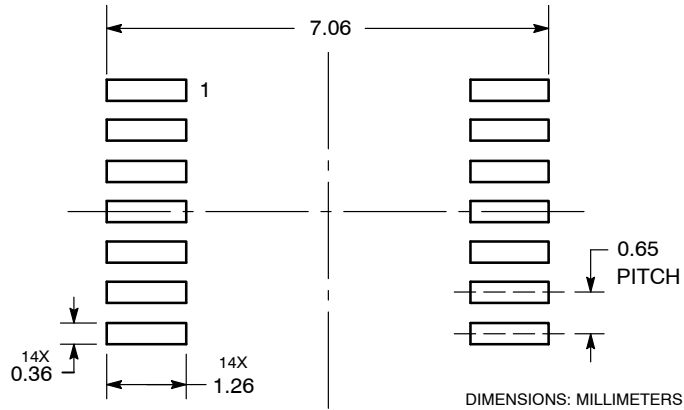
TSSOP-14  
CASE 948G-01  
ISSUE B



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -V-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

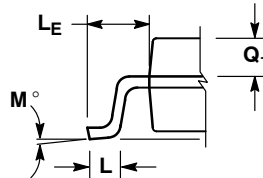
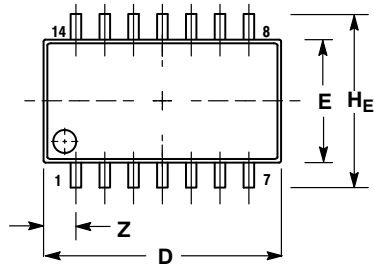
### SOLDERING FOOTPRINT



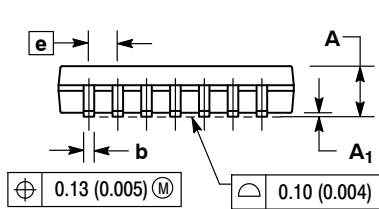
# MC74VHC00

## PACKAGE DIMENSIONS

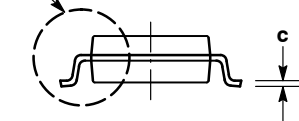
SOEIAJ-14  
CASE 965-01  
ISSUE B



DETAIL P



VIEW P



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H <sub>E</sub>	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L <sub>E</sub>	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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